

Advances in mirror technology for X-ray, EUV lithography, laser and other applications - 7-8 August 2003, San Diego, California, USA

SPIE - Dr. Eric Louis Profile

Description: -

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Holy Roman Empire.

State, The

Papacy

Philosophy, Medieval

Civilization, Medieval

Palézieux, Gérard de -- Catalogs.

Mexico -- Antiquities

Indians of Mexico -- Languages -- Writing

Manuscripts, Mexican

Optical radiometry -- Congresses

Optical coatings -- Congresses

Lasers -- Mirrors -- Design and construction -- Congresses

Mirrors -- Design and construction -- Congresses

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Microlithography: Science and Technology

Laser-Induced Damage in Optical Materials 7132 , 71320L, 2008. First, the

planar target is larger than the laser beam focus and a non-uniform temperature profile will be established that may be detrimental to in-band EUV emission.

Advances in mirror technology for X

Advanced automation and controls have been developed to provide the power and energy stability performance required during production fab operation. The ever-increasing demand on circuit performance necessitates rapid deployment of optical lithographic as well as early production next generation lithographic tools.

Front Matter: Volume 6702, Proceedings of SPIE

Additional topics include EUV source metrology and components collectors, electrodes , debris mitigation, and mechanisms of component erosion in EUV sources. The non-correctable added figure error is significantly better than required and the overall reflectance of the coatings with a special protective capping layer is 65%. Assembled EUV imaging systems have been evaluated by both visible-light and EUV interferometry.

Properties of ultrathin films appropriate for optics capping layers exposed to high energy photon irradiation

All data points show the dose-controlled in-band EUV power at the intermediate focus of the source module see figure.

λ	NA	I.F. (dia.) [*]	PO cross section	Reticle size
g	0.30	21.2		
	0.54			
i	0.54	24.8		
	0.57	31.2		
KrF	0.55			
	0.68	26.4		
ArF	0.75			
	0.85	27.6 (mm)		

^{*}Image field in diameter

Imaging performance with both conventional and off-axis illumination will be evaluated. Such plasmas are most efficiently excited by the relatively long, infrared wavelengths of CO₂-lasers, but a significant part of the rotational-vibrational excitation lines of the CO₂ radiation will be backscattered by the plasma's critical density surface and consequently will be present as parasitic radiation in the spectrum of such sources. Increasing spacing between dies on the wafer would prevent the unwanted exposure but results in an unacceptable loss of valuable wafer real estate thereby reducing the yield per wafer and is thus not a viable manufacturing solution.

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